PRODUCT NAME : BF422 NPN High Voltage Transistor (Pack of 5)

PRICE : Rs 39.00
SKU : RM1781

DESCRIPTION

Features

- Collector-Emitter Volt (Vceo): 250V
- Collector Current (Ic): 0.5A
- hfe: 50 @ 25mA
- Power Dissipation (Ptot): 625mW
- Current-Gain-Bandwidth (ftotal): 60MHz
- Type: PNP

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SEMICONDUCTOR TECHNICAL DATA

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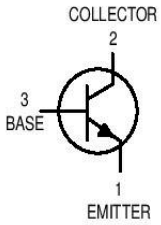
by BF420/D

High Voltage Transistors
NPN Silicon



BF420
BF422

CASE 29–04, STYLE 14
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	BF420	BF422	Unit
Collector–Emitter Voltage	V_{CEO}	300	250	Vdc
Collector–Base Voltage	V_{CBO}	300	250	Vdc
Emitter–Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage[1] (I_C = 1.0 mAdc, I_B = 0)	BF420 BF422	$V_{(BR)CEO}$	300 250	— —	Vdc
Collector–Base Breakdown Voltage (I_C = 100 µAdc, I_E = 0)	BF420 BF422	$V_{(BR)CBO}$	300 250	— —	Vdc
Emitter–Base Breakdown Voltage (I_E = 100 µAdc, I_C = 0)	BF420 BF422	$V_{(BR)EBO}$	5.0 5.0	— —	Vdc
Collector Cutoff Current (V_{CB} = 200 Vdc, I_E = 0)	BF420 BF422	I_{CBO}	— —	0.01 —	µAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)	BF420 BF422	I_{EBO}	— —	100 —	nAdc

1. Pulse Test: Pulse Width ≤ 300 µs; Duty Cycle ≤ 2.0%.

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